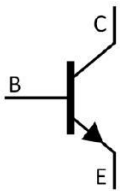


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Silicon NPN transistor in a SOT-323 Plastic Package.

High P_C and h_{FE} , excellent h_{FE} linearity, complementary pair with 9015W.

Low frequency, low noise pre-amplifier.



PIN1 Emitter PIN 2 Base PIN 3 Collector

h_{FE} Classifications Symbol	A	B	C	D
h_{FE} Range	60 150	100 300	200 600	400 1000
Marking	HJ6A	HJ6B	HJ6C	HJ6D

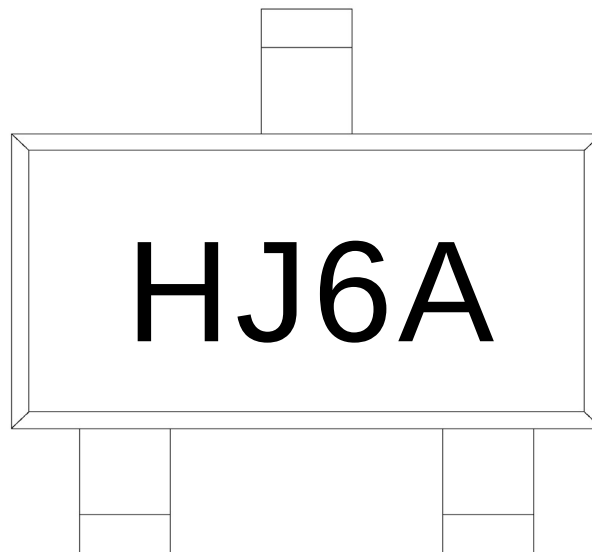
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Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	50	V
Collector to Emitter Voltage	V_{CEO}	45	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	100	mA
Collector Power Dissipation	P_C	250	mW
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=0.1mA$ $I_E=0$	50			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$ $I_B=0$	45			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=0.1mA$ $I_C=0$	5.0			V
Collector Cut-Off Current	I					

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Note:

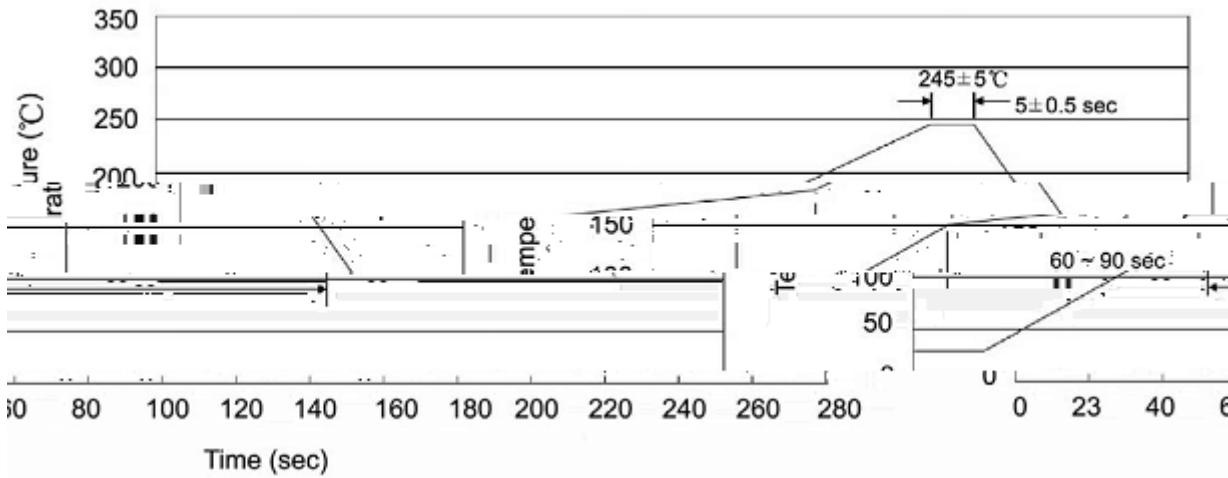
H: Company Code.

J6: Product Type.

A h_{FE} Classifications Symbol

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Whp shudwxuh Suriloh i ru LU Uhior z Vroghulqj+Se0luhh,



Note:

- | | | | | | |
|---|-----|-----|----|---------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245 | 5 | 5 | 0.5sec; | 2.Peak Temp.:245 5 , Duration:5 0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

260 5 10 1 sec. Temp.:260±5 Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOT-323	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205